TOSHIBA GTR MODULE SILICON N-CHANNEL IGBT

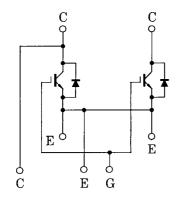
MG1200V1US51

HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

FEATURES

- High Input Impedance
- Enhancement Mode
- Electrodes are isolated from case.

EQUIVALENT CIRCUIT



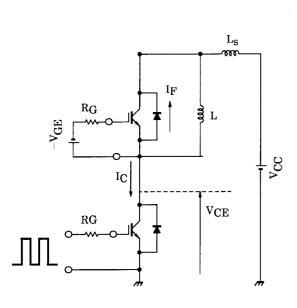
MAXIMUM RATINGS (Ta = 25°C)

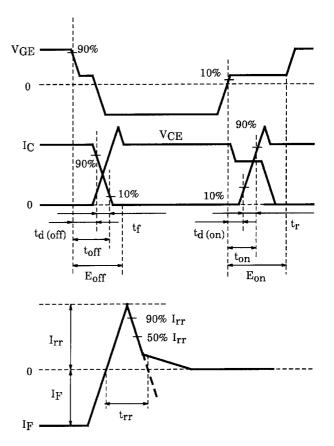
CHARACTERISTICS		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	1700	V	
Gate-Emitter Voltage		V _{GES}	20	V	
Collector Current	DC	Ι _C	1200	A	
	1ms	I _{CP}	2400		
Forward Current	DC	١ _F	1200	A	
	1ms	I _{FM}	2400		
Collector Power Dissipation (Tc = 25°C)		P _C	5560	W	
Junction Temperature		Tj	-20~125	°C	
Storage Temperature Range		T _{stg}	-40~125	°C	
Isolation Voltage		V _{Isol}	V _{Isol} 5400 (AC 1min)		
Screw Torque	Terminal: M4/M8		2/7	- N·m	
Sciew rolque	Mounting		4		

ELECTRICAL CHARACTERISTICS (Tc = 125°C : except thermal resistance)

CHARACTERISTICS		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Laekage Current		I _{GES}	V _{GE} = ±20 V, V _{CE} = 0 V	_	—	±50	nA
Collector Cut-Off Current		ICES	V _{CE} = 1700 V, V _{GE} = 0 V		_	100	mA
Gate-Emitter Cut-Off Voltage		V _{GE (off)}	V _{CE} = 5 V, I _C = 1.2 A	3.0	_	7.0	V
Collecter-Emitter Saturation Voltage		V _{CE (sat)}	V _{GE} = 15 V, I _C = 1200 A		_	5.0	V
Input Capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0 V, f = 300 kHz	_	130	_	nF
Switching Time (Note 1)	Rise Time	tr			_	0.7	μs
	Turn-On Time	t _{on}	$V_{CC} = 900 \text{ V}, \text{ I}_{C} = 1200 \text{ A}$		_	1.0	μs
	Fall Time	t _f	$V_{GE} = \pm 15 \text{ V}, \text{ R}_{G} = 1.8 \Omega$ (Inductive load: Ls = 150 nH)		_	0.8	μs
	Turn-Off Time	t _{off}			_	1.5	μs
Forward Voltage		V _F	I _F = 1200 A, V _{GE} = 0 V		_	3.2	V
Reverse Recovery Time (Note 1)		t _{rr}	I _F = 1200 A, V _{GE} = 15 V di/dt = 4000 A/µs, V _{CC} = 900 V	_	_	0.8	μs
Switching Dissipation (Note 1)	Turn-On Loss	Eon	V _{CC} = 900 V, I _C = 1200 A		250	_	mJ
	Turn-Off Loss	Eoff	$V_{GE} = \pm 15 \text{ V}, \text{ R}_{G} = 1.8 \Omega$		500	_	mJ
	Diode Loss	Edsw	I _F = 1200 A, V _{GE} = -15 V di/dt = 4000 A/µs, V _{CC} = 900 V	_	300	_	mJ
Thermal Resistance		R _{th (j−c)}	Transistor (IGBT) Stage	_	_	0.018	°C/W
			Diode Stage	_	—	0.035	°C/W

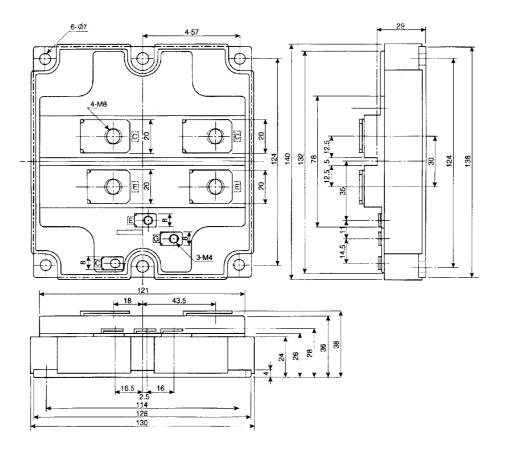
Note 1: Test circuit and timing chart of switching time, reverse recovery time and switching dissipation.





PACKAGE DIMENSIONS: TOSHIBA 2-142A1A

Unit: mm



Weight: 900 g (typ.)

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